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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

FAIRCHILD SEMICONDUCTOR®

December 2013

SGH10N60RUFD

600V, 10 A Short Circuit Rated IGBT

Features

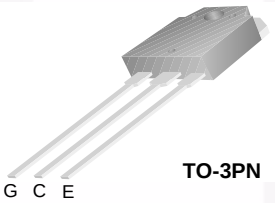
- Short Circuit Rated 10 us @ T_C = 100°C, V_{GE} = 15 V
- High Speed Switching
- Low Saturation Voltage : $V_{CE(sat)}$ = 2.2 V @ I_C = 10 A
- High Input Impedance
- CO-PAK, IGBT with FRD : t_{rr} = 42 ns (typ.)

Description

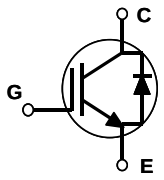
Fairchild's RUFD series of insulated gate bipolar transistors (IGBTs) provide low conduction and switching losses as well as short circuit ruggedness. The RUFD series is designed for applications such as motor control, uninterrupted power supplies (UPS) and general inverters where short circuit ruggedness is a required feature.

Applications

AC & DC Motors Controls, General Purpose Inverters, and Robotics, and Servo Controls



TO-3PN



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted.

Symbol	Description		Ratings	Unit
V_{CES}	Collector-Emitter Voltage		600	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Collector Current	@ T_C = 25°C	16	A
	Collector Current	@ T_C = 100°C	10	A
$I_{CM\ (1)}$	Pulsed Collector Current		30	A
I_F	Diode Continuous Forward Current	@ T_C = 100°C	12	A
I_{FM}	Diode Maximum Forward Current		92	A
T_{SC}	Short Circuit Withstand Time	@ T_C = 100°C	10	us
P_D	Maximum Power Dissipation	@ T_C = 25°C	75	W
	Maximum Power Dissipation	@ T_C = 100°C	30	W
T_J	Operating Junction Temperature		-55 to +150	°C
T_{stg}	Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds		300	°C

Notes :
(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$(IGBT)	Thermal Resistance, Junction-to-Case	--	1.6	°C/W
$R_{\theta JC}$(DIODE)	Thermal Resistance, Junction-to-Case	--	2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
SGH10N60RUFD	SGH10N60RUFD	TO-3PN	Tube	N/A	N/A	30 units

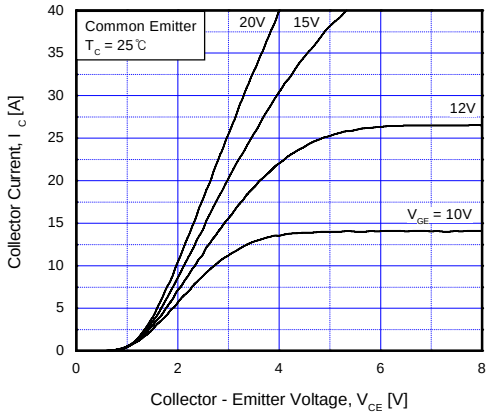
Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{CES}	Collector-Emitter Breakdown Voltage	V_{GE} = 0 V, I_C = 250 uA	600	--	--	V
ΔB_{VCES} / ΔT_J	Temperature Coefficient of Breakdown Voltage	V_{GE} = 0 V, I_C = 1 mA	--	0.6	--	V/°C
I_{CES}	Collector Cut-Off Current	V_{CE} = V_{CES}, V_{GE} = 0 V	--	--	250	uA
I_{GES}	G-E Leakage Current	V_{GE} = V_{GES}, V_{CE} = 0 V	--	--	± 100	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	I_C = 10 mA, V_{CE} = V_{GE}	5.0	6.0	8.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	I_C = 10 A, V_{GE} = 15 V	--	2.2	2.8	V
		I_C = 16 A, V_{GE} = 15 V	--	2.5	--	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	V_{CE} = 30 V, V_{GE} = 0 V, f = 1 MHz	--	660	--	pF
C_{oes}	Output Capacitance		--	115	--	pF
C_{res}	Reverse Transfer Capacitance		--	25	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 300 V, I_C = 10 A, R_G = 20 Ω, V_{GE} = 15 V, Inductive Load, T_C = 25°C	--	15	--	ns
t_r	Rise Time		--	30	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	36	50	ns
t_f	Fall Time		--	158	200	ns
E_{on}	Turn-On Switching Loss		--	141	--	uJ
E_{off}	Turn-Off Switching Loss		--	215	--	uJ
E_{ts}	Total Switching Loss		--	356	500	uJ
$t_{d(on)}$	Turn-On Delay Time	V_{CC} = 300 V, I_C = 10 A, R_G = 20Ω, V_{GE} = 15 V, Inductive Load, T_C = 125°C	--	16	--	ns
t_r	Rise Time		--	33	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	42	60	ns
t_f	Fall Time		--	242	350	ns
E_{on}	Turn-On Switching Loss		--	161	--	uJ
E_{off}	Turn-Off Switching Loss		--	452	--	uJ
E_{ts}	Total Switching Loss		--	613	860	uJ
T_{sc}	Short Circuit Withstand Time	V_{CC} = 300 V, V_{GE} = 15 V @ T_C = 100°C	10	--	--	us
Q_g	Total Gate Charge	V_{CE} = 300 V, I_C = 10 A, V_{GE} = 15 V	--	30	45	nC
Q_{ge}	Gate-Emitter Charge		--	5	10	nC
Q_{gc}	Gate-Collector Charge		--	8	16	nC
L_e	Internal Emitter Inductance	Measured 5mm from PKG	--	14	--	nH

Electrical Characteristics of DIODE T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
V_{FM}	Diode Forward Voltage	I_F = 12 A	T_C = 25°C	--	1.4	1.7	V
			T_C = 100°C	--	1.3	--	
t_{rr}	Diode Reverse Recovery Time	I_F = 12 A, di/dt = 200 A/us	T_C = 25°C	--	42	60	ns
			T_C = 100°C	--	60	--	
I_{rr}	Diode Peak Reverse Recovery Current		T_C = 25°C	--	3.5	6.0	A
			T_C = 100°C	--	5.6	--	
Q_{rr}	Diode Reverse Recovery Charge		T_C = 25°C	--	80	180	nC
			T_C = 100°C	--	220	--	

Typical Characteristics



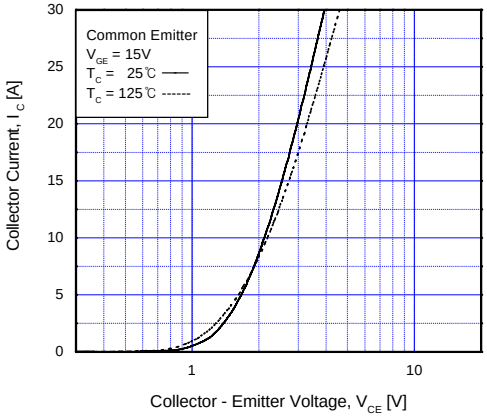


Fig 1. Typical Output Characteristics

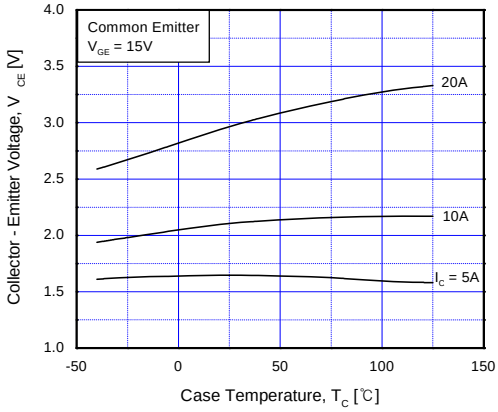


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

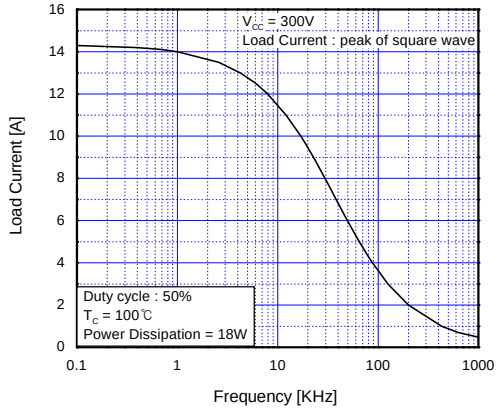


Fig 4. Load Current vs. Frequency

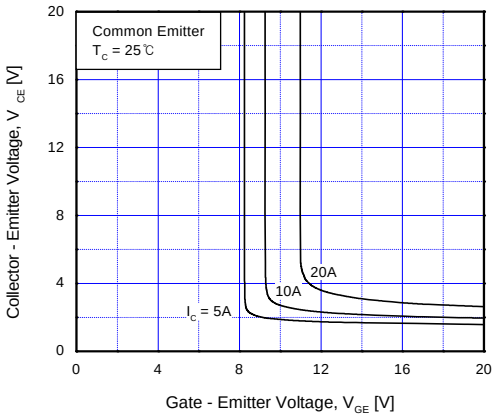


Fig 5. Saturation Voltage vs. V_{GE}

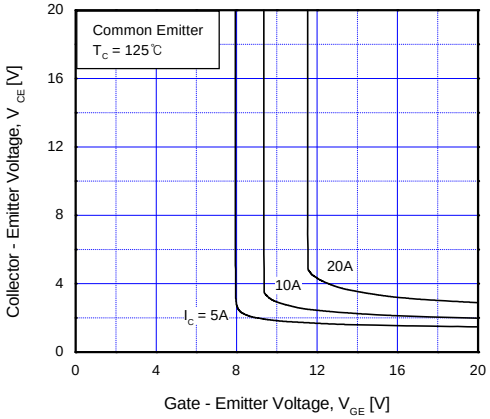


Fig 6. Saturation Voltage vs. V_{GE}

Typical Characteristics (continued)

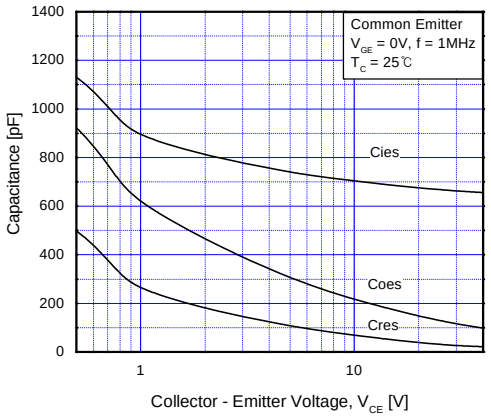


Fig 7. Capacitance Characteristics

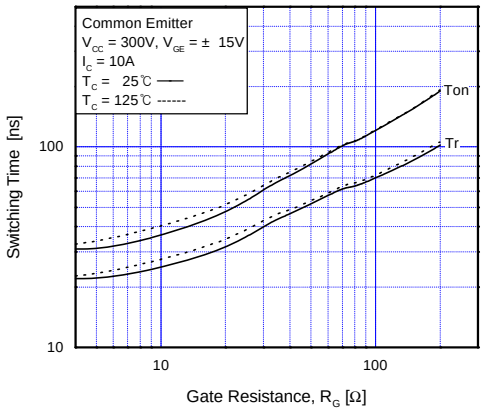


Fig 8. Turn-On Characteristics vs. Gate Resistance

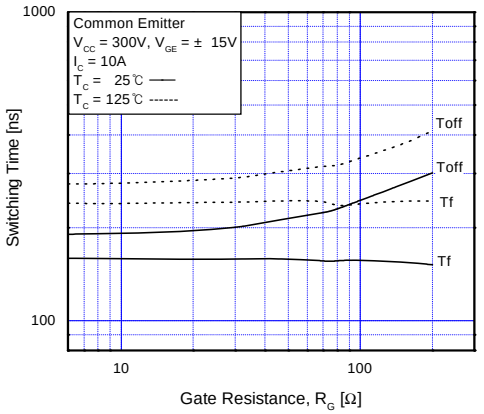


Fig 9. Turn-Off Characteristics vs. Gate Resistance

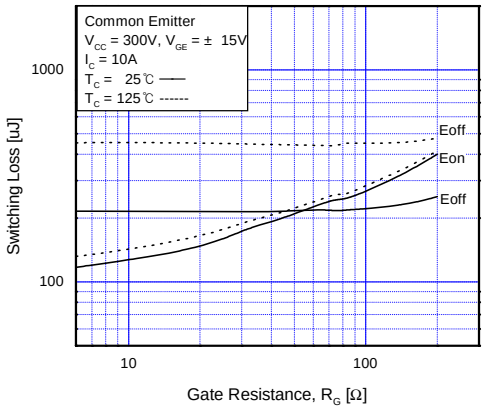


Fig 10. Switching Loss vs. Gate Resistance

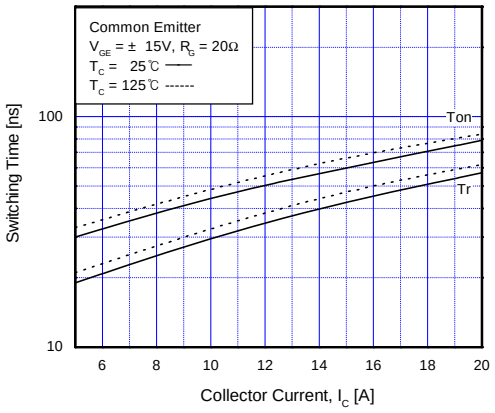


Fig 11. Turn-On Characteristics vs. Collector Current

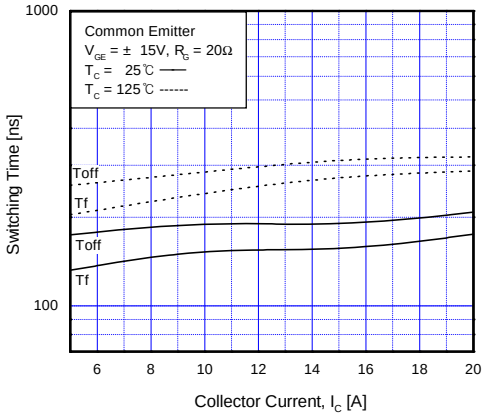


Fig 12. Turn-Off Characteristics vs. Collector Current

Typical Characteristics (continued)

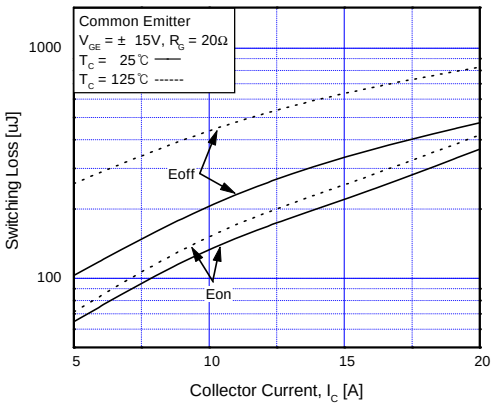


Fig 13. Switching Loss vs. Collector Current

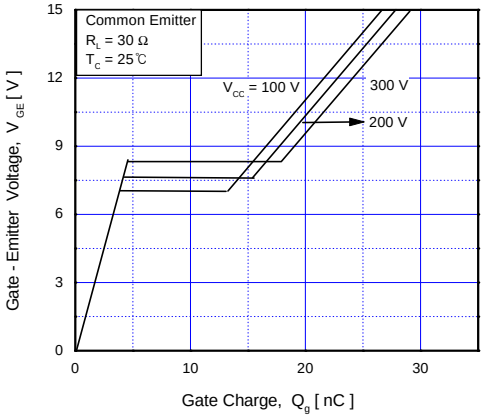


Fig 14. Gate Charge Characteristics

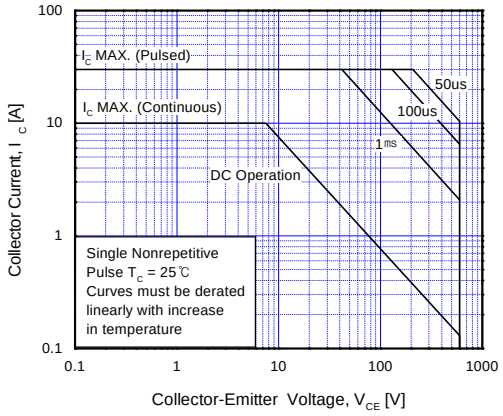


Fig 15. SOA Characteristics

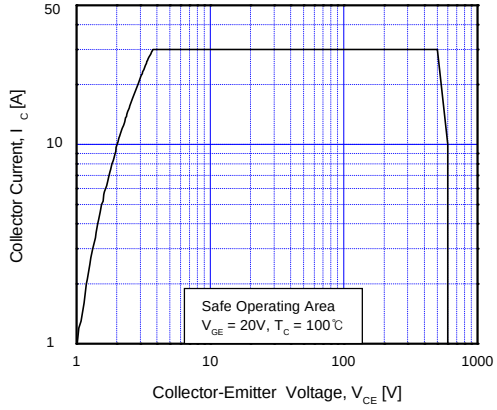


Fig 16. Turn-Off SOA Characteristics

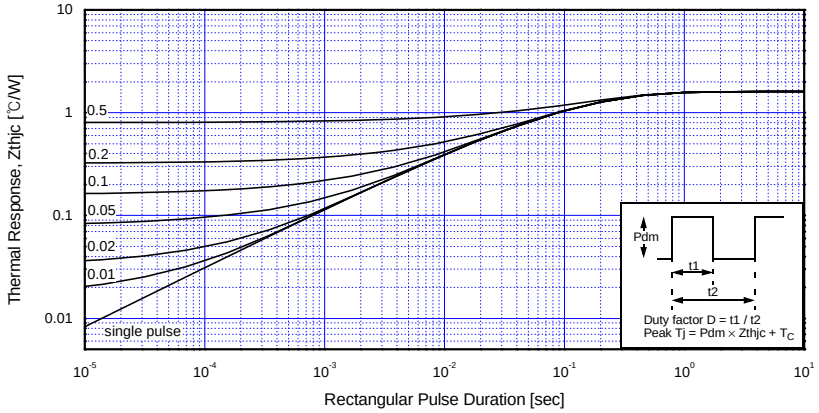


Fig 17. Transient Thermal Impedance of IGBT

Typical Characteristics (continued)

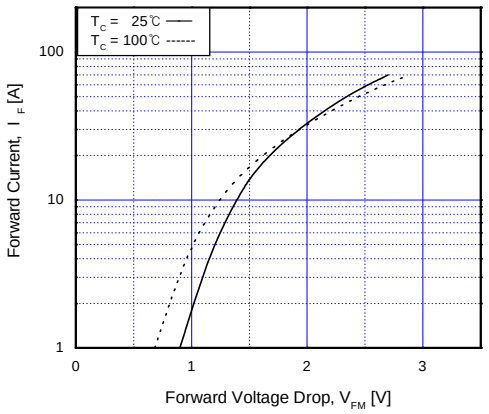


Fig 18. Forward Characteristics

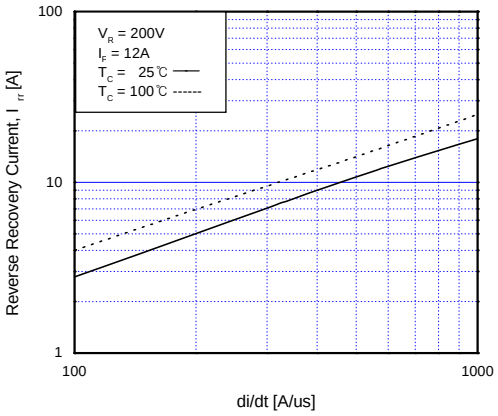


Fig 19. Reverse Recovery Current

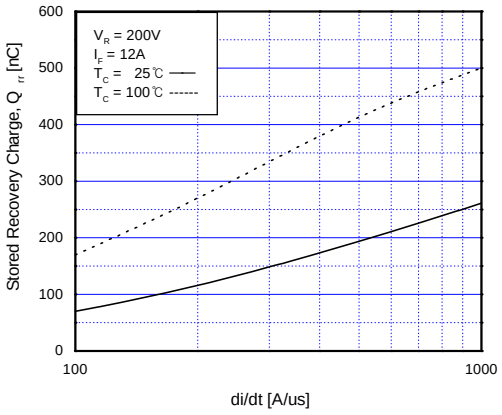


Fig 20. Stored Charge

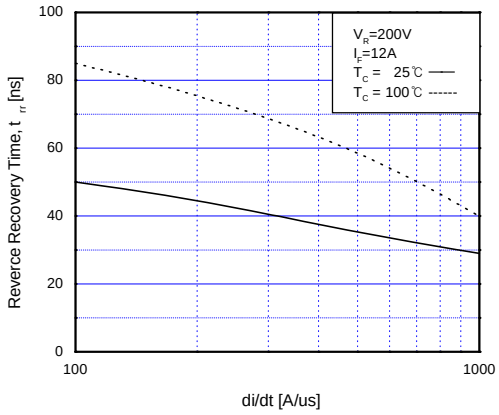


Fig 21. Reverse Recovery Time

Mechanical Dimensions

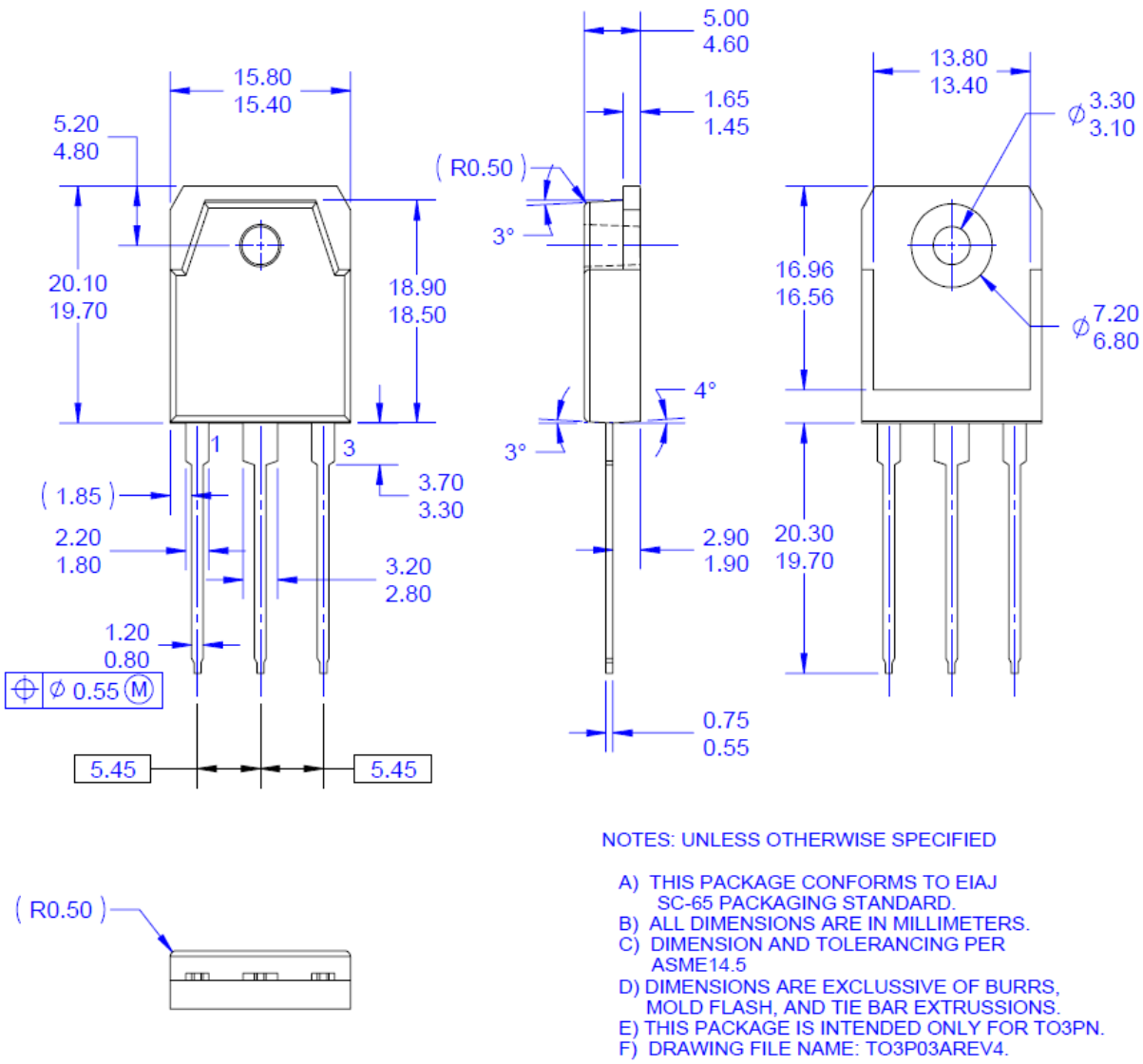


Figure 22. TO3, 3-Lead, Plastic, EIAJ SC-65

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Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I66

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